

SOT-89 NPN Silicon NPN transistor in a SOT-89 Plastic Package.

, , 2SA1797
 Low saturation voltage, excellent DC current gain characteristics, complements the 2SA1797.
 HF product.

Low frequency power amplifier applications.



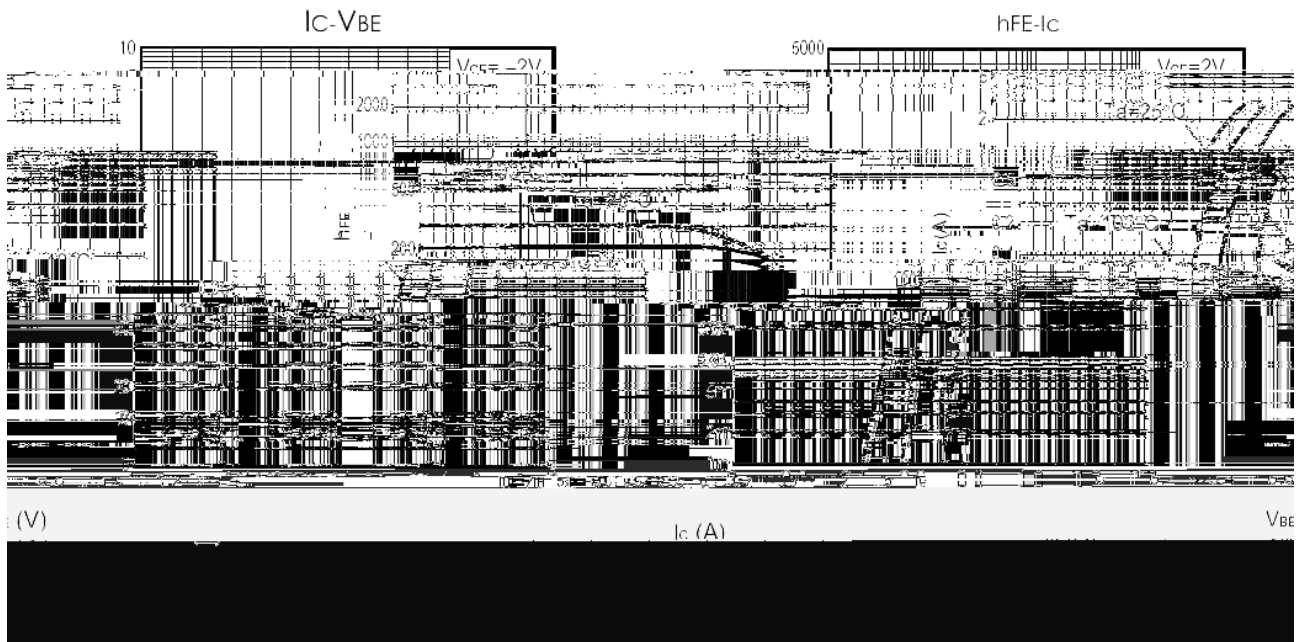
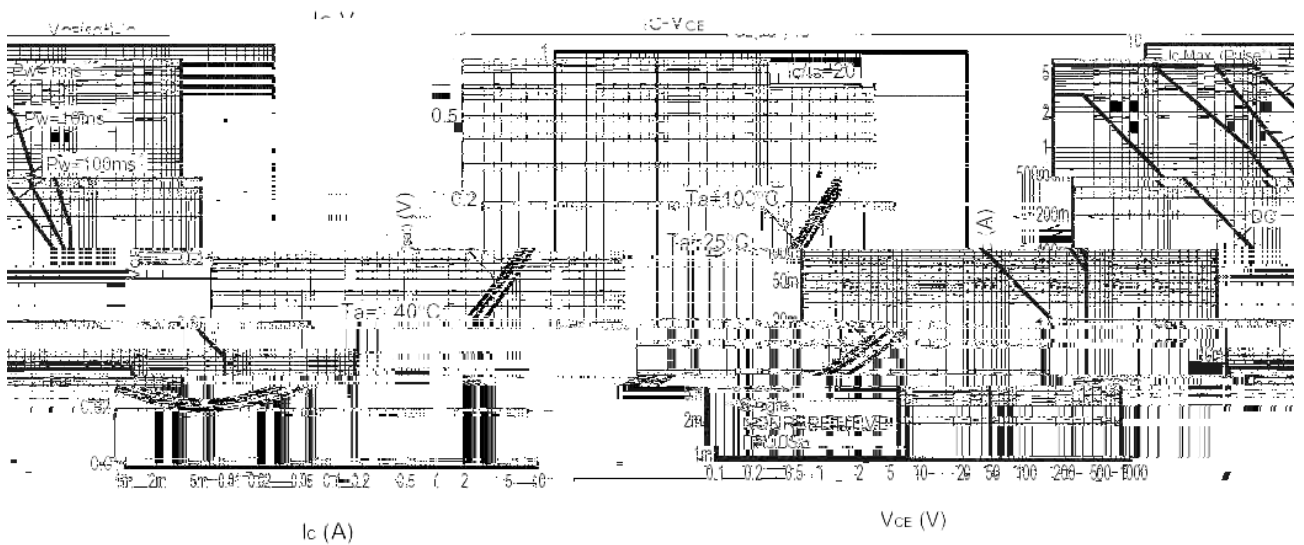
PIN1 Base PIN 2 Collector PIN 3 Emitter

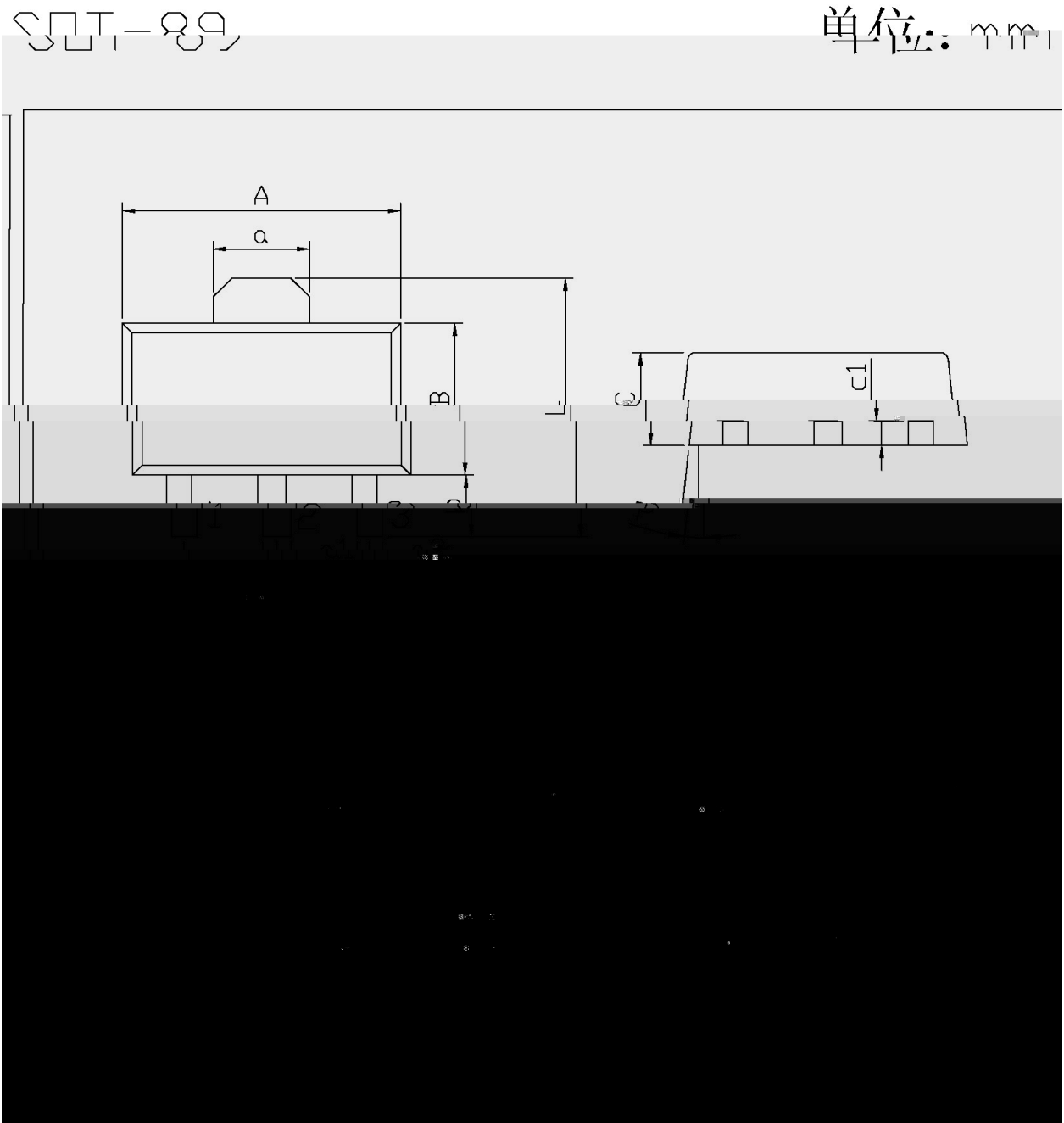
h_{FE} Classifications Symbol	P	Q
h_{FE} Range	82 180	120 270
Marking	HDKP	HDKQ

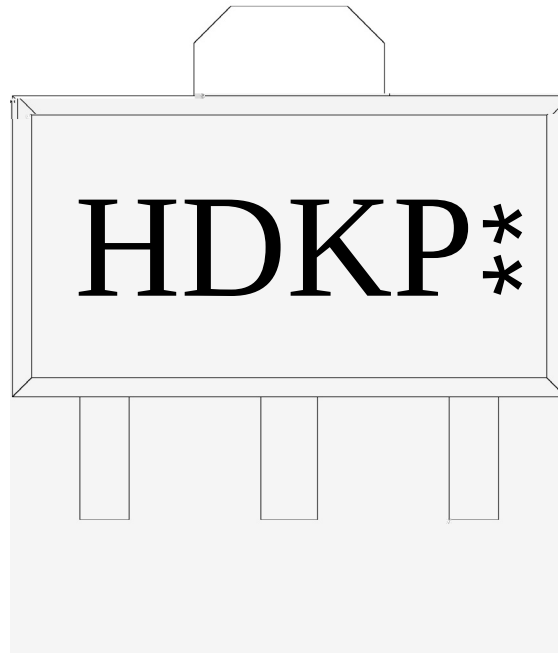
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	3.0	A
Collector Current – Continuous(Pulse)	I_{CP}	6.0	A
Collector Power Dissipation	P_C	0.5	W
Collector Power Dissipation*	$*P_C$	2.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

* $40 \times 40 \times 0.7$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=50\mu A$	60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$	50			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=50\mu A$	6.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=60V$			0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$			0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=2.0V$ $I_C=500mA$	82		270	
	$h_{FE(2)}$	$V_{CE}=2.0V$ $I_C=1.5A$	45			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1.0A$ $I_B=50mA$		0.13	0.35	V
Transition Frequency	f_T	$V_{CE}=2.0V$ $I_C=0.5A$ $f=100MHz$		210		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V$ $f=1.0MHz$		25		pF







H

DK

P

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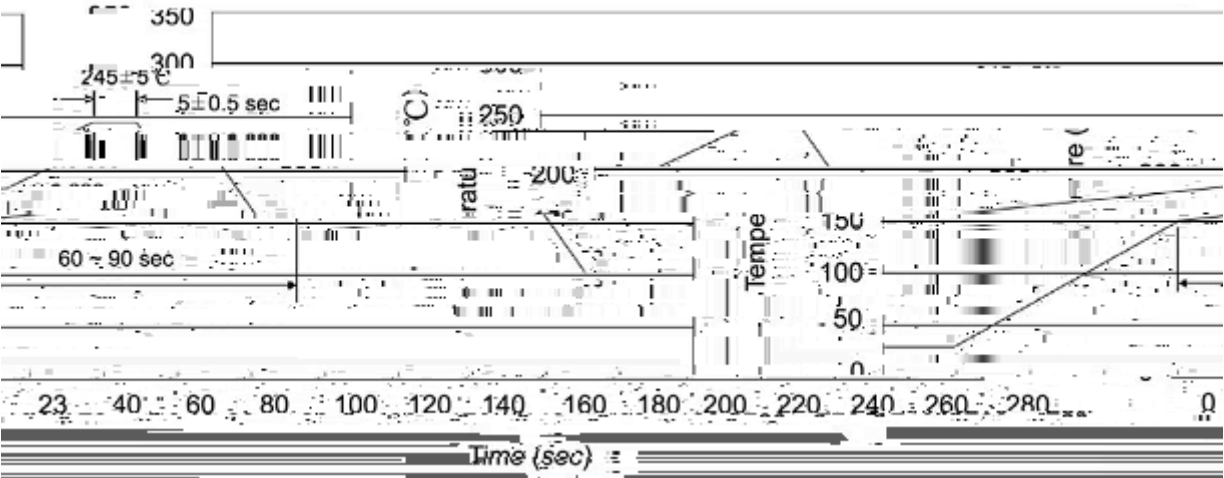
Note:

H: Company Code.

DK: Product Type.

P h_{FE} Classifications Symbol

**: Lot No. Code, code change with Lot No.



9 N

Note:

- 1

25 150

60 90sec;
- 2

245±5

5±0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:245±5

, Duration:5±0.5sec.
3. Cooling Speed: 2~10

/sec.

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱